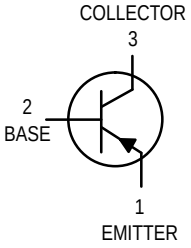
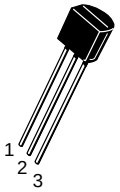
Amplifier Transistors

PNP Silicon

2N4125
2N4126





CASE 29–04, STYLE 1
TO–92 (TO–226AA)

MAXIMUM RATINGS

Rating	Symbol	2N4125	2N4126	Unit
Collector–Emitter Voltage	V_{CEO}	30	25	Vdc
Collector–Base Voltage	V_{CBO}	30	25	Vdc
Emitter–Base Voltage	V_{EBO}	4.0		Vdc
Collector Current — Continuous	I_C	200		mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	625 5.0		mW mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	1.5 12		Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage(1) (I_C = 1.0 mAdc, I_B = 0)	 2N4125 2N4126	$V_{(BR)CEO}$	 30 25	 — —	Vdc
Collector–Base Breakdown Voltage (I_C = 10 μAdc, I_E = 0)	 2N4125 2N4126	$V_{(BR)CBO}$	 30 25	 — —	Vdc
Emitter–Base Breakdown Voltage (I_E = 10 μAdc, I_C = 0)		$V_{(BR)EBO}$	4.0	—	Vdc
Collector Cutoff Current (V_{CB} = 20 Vdc, I_E = 0)		I_{CBO}	—	50	nAdc
Emitter Cutoff Current (V_{EB} = 3.0 Vdc, I_C = 0)		I_{EBO}	—	50	nAdc

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle = 2.0%.

REV 1

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Continued)

Characteristic		Symbol	Min	Max	Unit
ON CHARACTERISTICS					
DC Current Gain(1)		h_{FE}			—
(I_C = 2.0 mAdc, V_{CE} = 1.0 Vdc)	2N4125		50	150	
	2N4126		120	360	
(I_C = 50 mAdc, V_{CE} = 1.0 Vdc)	2N4125		25	—	
	2N4126		60	—	
Collector–Emitter Saturation Voltage(1) (I_C = 50 mAdc, I_B = 5.0 mAdc)		$V_{CE(sat)}$	—	0.4	Vdc
Base–Emitter Saturation Voltage(1) (I_C = 50 mAdc, I_B = 5.0 mAdc)		$V_{BE(sat)}$	—	0.95	Vdc
SMALL–SIGNAL CHARACTERISTICS					
Current–Gain — Bandwidth Product		f_T			MHz
(I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	2N4125		200	—	
	2N4126		250	—	
Input Capacitance (V_{EB} = 0.5 Vdc, I_C = 0, f = 1.0 MHz)		C_{ibo}	—	10	pF
Collector–Base Capacitance (V_{CB} = 5.0 Vdc, I_E = 0, f = 1.0 MHz)		C_{cb}	—	4.5	pF
Small–Signal Current Gain		h_{fe}			—
(I_C = 2.0 mAdc, V_{CE} = 10 Vdc, f = 1.0 kHz)	2N4125		50	200	
	2N4126		120	480	
Current Gain — High Frequency		$\|h_{fe}\|$			—
(I_C = 10 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	2N4125		2.0	—	
	2N4126		2.5	—	
Noise Figure		NF			dB
(I_C = 100 μAdc, V_{CE} = 5.0 Vdc, R_S = 1.0 k ohm,	2N4125		—	5.0	
f = 1.0 kHz)	2N4126		—	4.0	

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle = 2.0%.

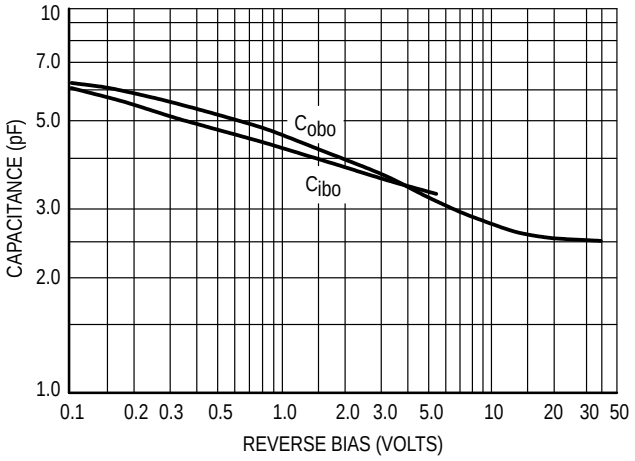


Figure 1. Capacitance

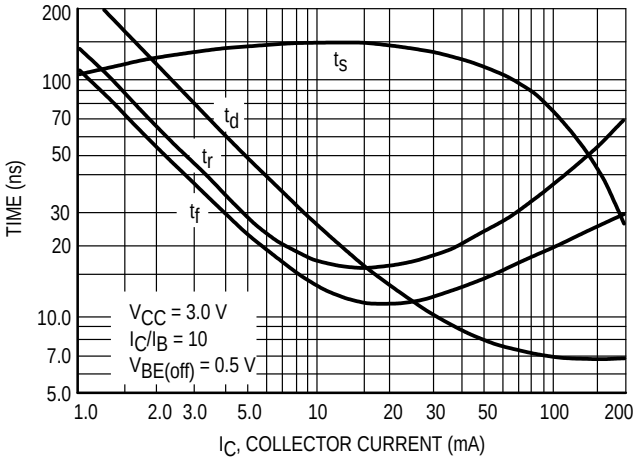


Figure 2. Switching Times

AUDIO SMALL–SIGNAL CHARACTERISTICS

NOISE FIGURE

V_{CE} = –5.0 Vdc, T_A = 25°C
Bandwidth = 1.0 Hz

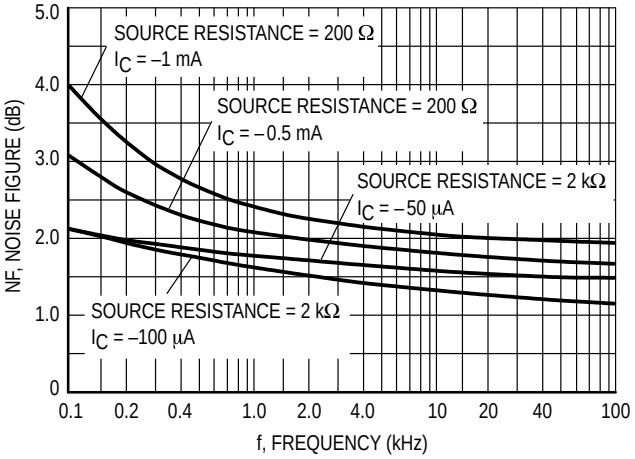


Figure 3. Frequency Variations

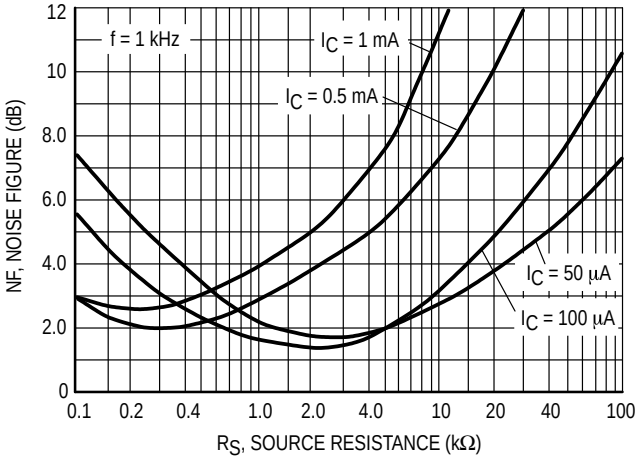


Figure 4. Source Resistance

h PARAMETERS

V_{CE} = 10 V, f = 1 kHz, T_A = 25°C

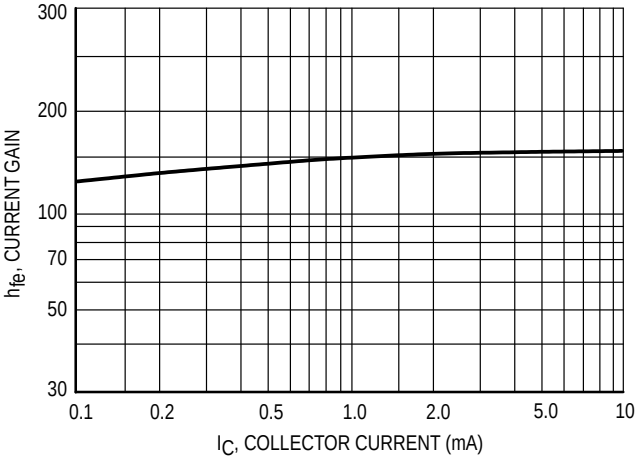


Figure 5. Current Gain

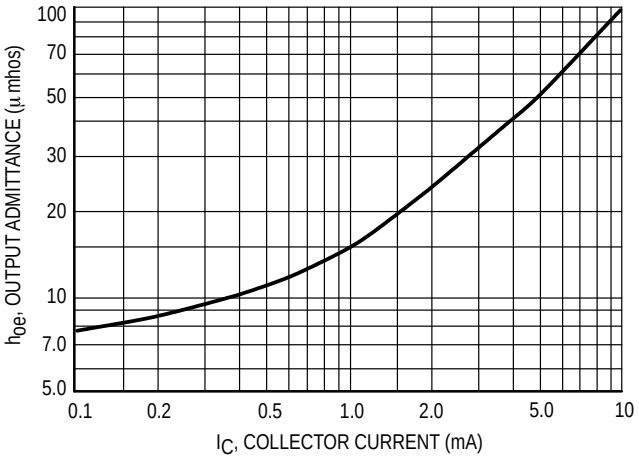


Figure 6. Output Admittance

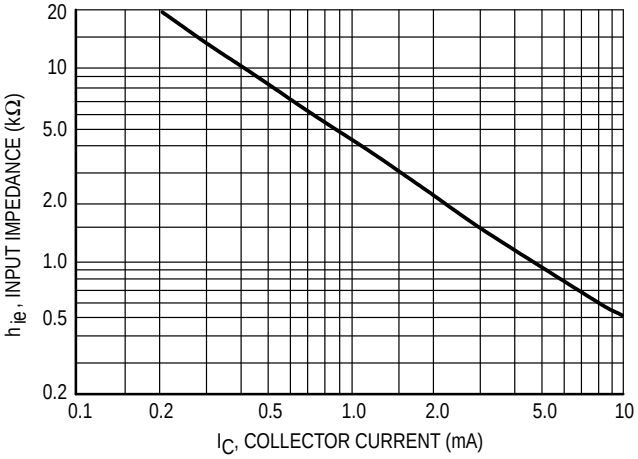


Figure 7. Input Impedance

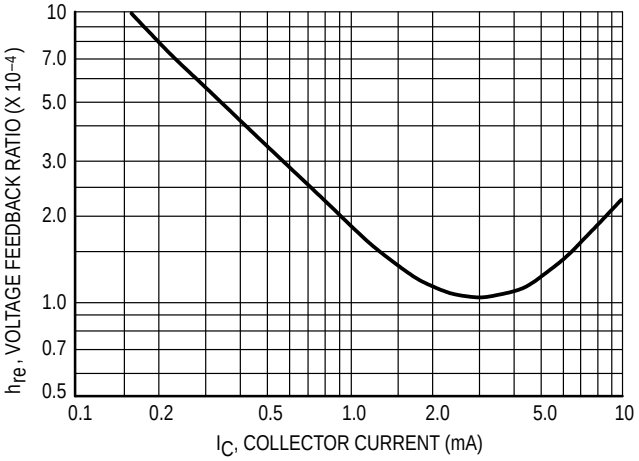


Figure 8. Voltage Feedback Ratio

STATIC CHARACTERISTICS

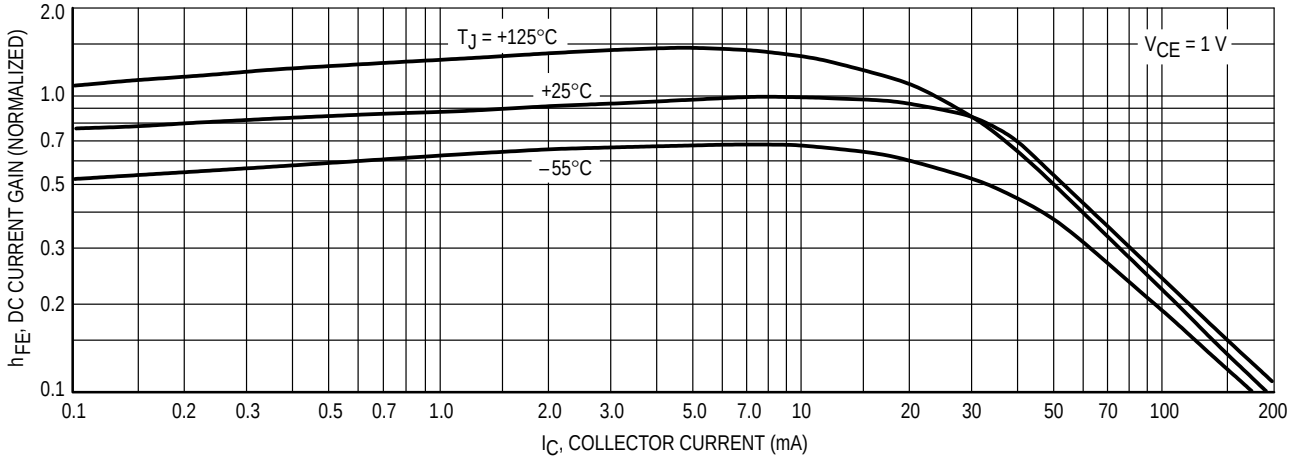


Figure 9. DC Current Gain

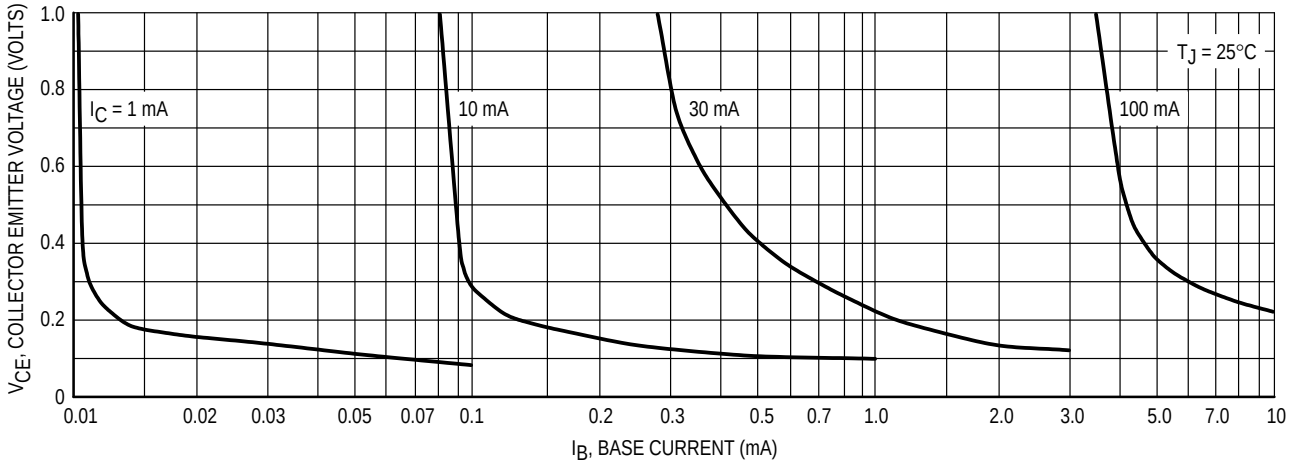


Figure 10. Collector Saturation Region

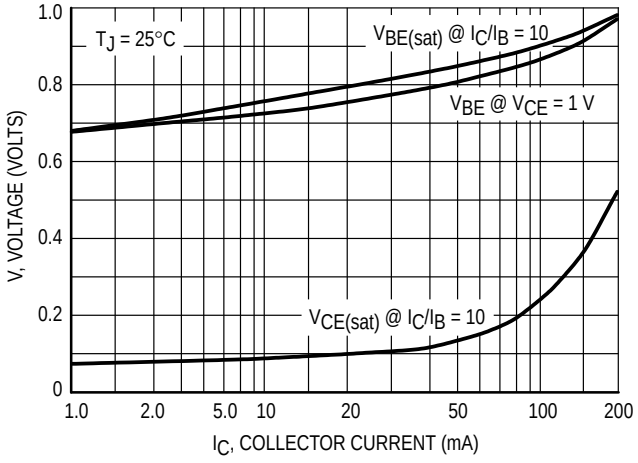


Figure 11. “On” Voltages

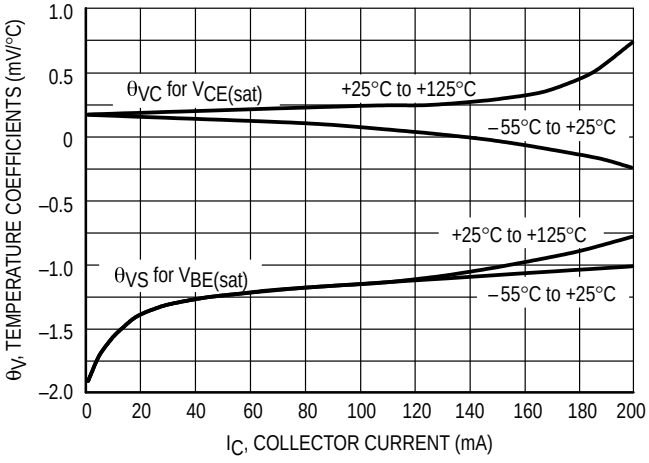
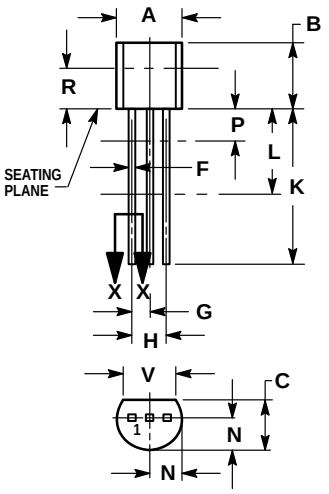
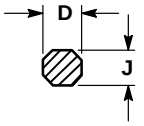


Figure 12. Temperature Coefficients

PACKAGE DIMENSIONS





SECTION X–X

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSION D AND J APPLY BETWEEN L AND K MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.022	0.41	0.55
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	—	12.70	—
L	0.250	—	6.35	—
N	0.080	0.105	2.04	2.66
P	—	0.100	—	2.54
R	0.115	—	2.93	—
V	0.135	—	3.43	—

CASE 029–04
(TO–226AA)
ISSUE AD

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

How to reach us:
USA/EUROPE: Motorola Literature Distribution;
P.O. Box 20912; Phoenix, Arizona 85036. 1–800–441–2447

MFAX: RMFAX0@email.sps.mot.com – TOUCHTONE (602) 244–6609
INTERNET: http://Design–NET.com

JAPAN: Nippon Motorola Ltd.; Tatsumi–SPD–JLDC, Toshikatsu Otsuki,
6F Seibu–Butsuryu–Center, 3–14–2 Tatsumi Koto–Ku, Tokyo 135, Japan. 03–3521–8315

HONG KONG: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park,
51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852–26629298